International
IOR Rectifier

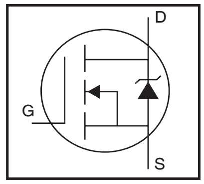
AUTOMOTIVE GRADE

PD - 97624

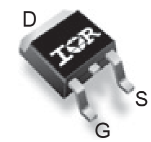
AUIRLR120N

HEXFET® Power MOSFET

- Advanced Planar Technology
- Logic-Level Gate Drive
- Low On-Resistance
- Dynamic dV/dT Rating
- 175ºC Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified*



$V_{(BR)DSS}$	100V
$R_{DS(on)}$ max.	0.185Ω
I_D	10A



D-Pak
AUIRLR120N

G	D	S
Gate	Drain	Source

Description

Specifically designed for Automotive applications, this cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	10	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	7.0	
I_{DM}	Pulsed Drain Current ①	35	
P_D @T_C = 25°C	Power Dissipation	48	W
	Linear Derating Factor	0.32	W/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
E_{AS}	Single Pulse Avalanche Energy (Thermally Limited)②	85	mJ
I_{AR}	Avalanche Current ①	6.0	A
E_{AR}	Repetitive Avalanche Energy ①	4.8	mJ
dv/dt	Peak Diode Recovery ③	5.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	

Thermal Resistance

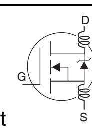
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑤	——	3.1	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount) **	——	50	
$R_{\theta JA}$	Junction-to-Ambient	——	110	

*Qualification standards can be found at http://www.irf.com/

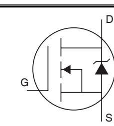
Static Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	–––	–––	V	V_{GS} = 0V, I_D = 250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	–––	0.12	–––	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	–––	–––	0.185	Ω	V_{GS} = 10V, I_D = 6.0A ④
		–––	–––	0.225		V_{GS} = 5.0V, I_D = 6.0A ④
		–––	–––	0.265		V_{GS} = 4.0V, I_D = 5.0A ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	–––	2.0	V	V_{DS} = V_{GS}, I_D = 250μA
gfs	Forward Transconductance	3.1	–––	–––	S	V_{DS} = 25V, I_D = 6.0A
I_{DSS}	Drain-to-Source Leakage Current	–––	–––	25	μA	V_{DS} = 100V, V_{GS} = 0V
		–––	–––	250		V_{DS} = 80V, V_{GS} = 0V, T_J = 150°C
I_{GSS}	Gate-to-Source Forward Leakage	–––	–––	100	nA	V_{GS} = 16V
	Gate-to-Source Reverse Leakage	–––	–––	-100		V_{GS} = -16V

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge	–––	–––	20	nC	I_D = 6.0A
Q_{gs}	Gate-to-Source Charge	–––	–––	4.6		V_{DS} = 80V
Q_{gd}	Gate-to-Drain ("Miller") Charge	–––	–––	10		V_{GS} = 5.0V, See Fig. 6 & 13 ④
$t_{d(on)}$	Turn-On Delay Time	–––	4.0	–––	ns	V_{DD} = 50V
t_r	Rise Time	–––	35	–––		I_D = 6.0A
$t_{d(off)}$	Turn-Off Delay Time	–––	23	–––		R_G = 11Ω, V_{GS} = 5.0V,
t_f	Fall Time	–––	22	–––		R_D = 8.2Ω, See Fig. 10 ④
L_D	Internal Drain Inductance	–––	4.5	–––	nH	Between lead, 6mm (0.25in.) 
L_S	Internal Source Inductance	–––	7.5	–––		from package and center of die contact
C_{iss}	Input Capacitance	–––	440	–––	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	–––	97	–––		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	–––	50	–––		f = 1.0MHz, See Fig. 5

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	–––	–––	10	A	MOSFET symbol showing the 
I_{SM}	Pulsed Source Current (Body Diode) ①	–––	–––	35		integral reverse p-n junction diode.
V_{SD}	Diode Forward Voltage	–––	–––	1.3	V	T_J = 25°C, I_S = 6.0A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	–––	110	160	ns	T_J = 25°C, I_F = 6.0A
Q_{rr}	Reverse Recovery Charge	–––	410	620	nC	di/dt = 100A/μs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② V_{DD} = 25V, starting T_J = 25°C, L = 4.7mH R_G = 25Ω, I_{AS} = 6.0A. (See Figure 12)

③ $I_{SD} \le$ 6.0A, di/dt $\le$ 340A/μs, $V_{DD} \le V_{(BR)DSS}$, $T_J \le$ 175°C

④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

⑤ R_θ is measured at T_J approximately 90°C.

** When mounted on 1" square PCB (FR-4 or G-10 Material) .
For recommended footprint and soldering techniques refer to application note #AN-994

Qualification Information†

Qualification Level		Automotive (per AEC-Q101) ††	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		D-PAK	MSL1
ESD	Machine Model	Class M2 (+/- 150V) ††† AEC-Q101-002	
	Human Body Model	Class H1A (+/- 500V) ††† AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 2000V) ††† AEC-Q101-005	
RoHS Compliant		Yes	

† Qualification standards can be found at International Rectifier's web site: http//www.irf.com/

†† Exceptions to AEC-Q101 requirements are noted in the qualification report.

††† Highest passing voltage.

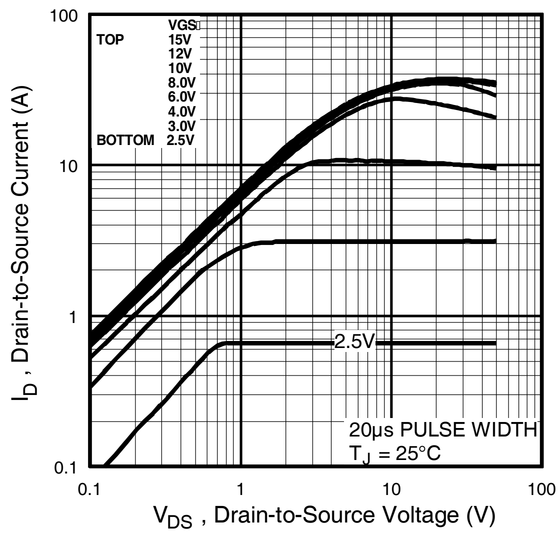


Fig 1. Typical Output Characteristics

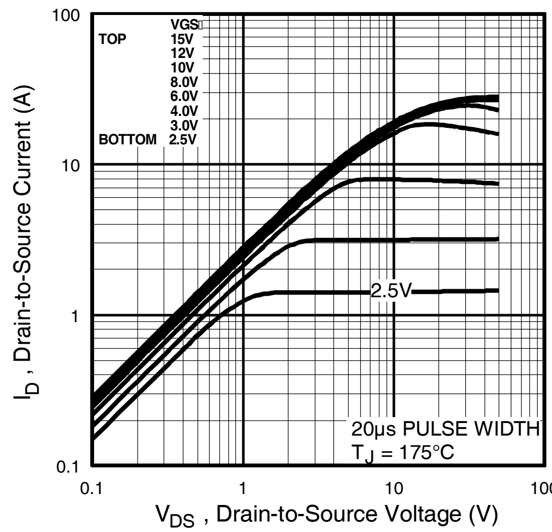


Fig 2. Typical Output Characteristics

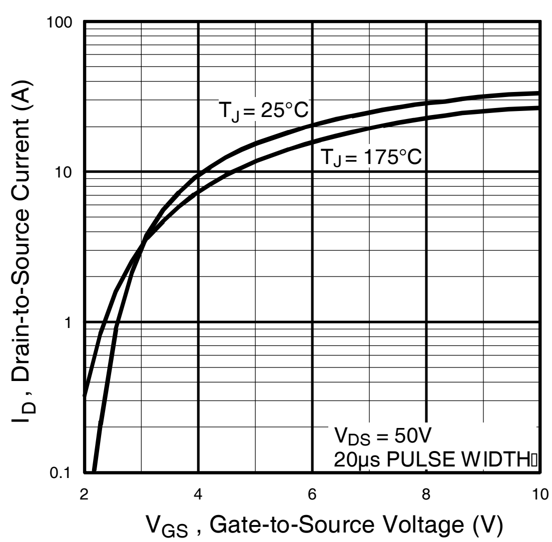


Fig 3. Typical Transfer Characteristics

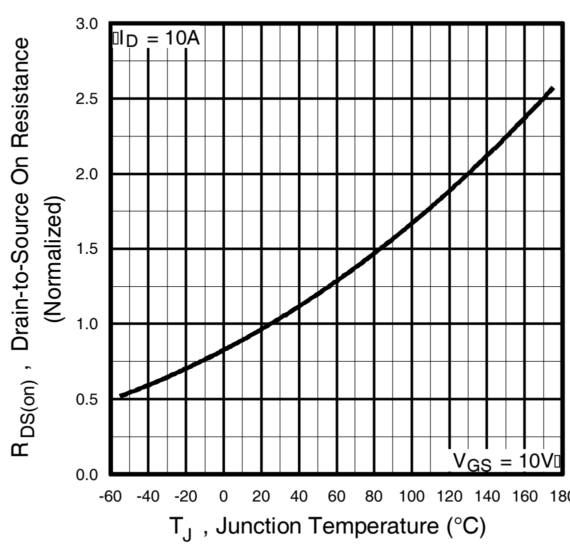


Fig 4. Normalized On-Resistance Vs. Temperature

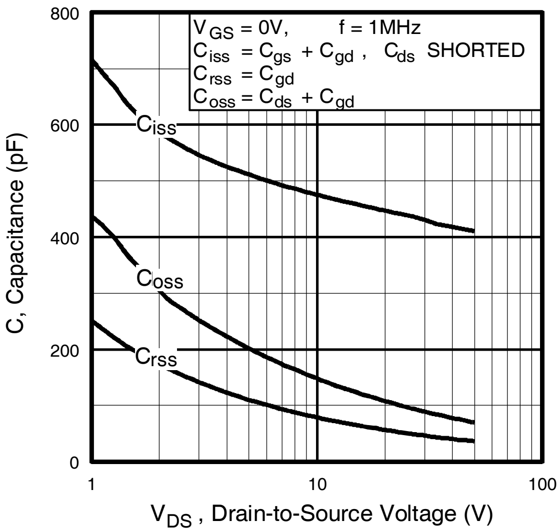


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

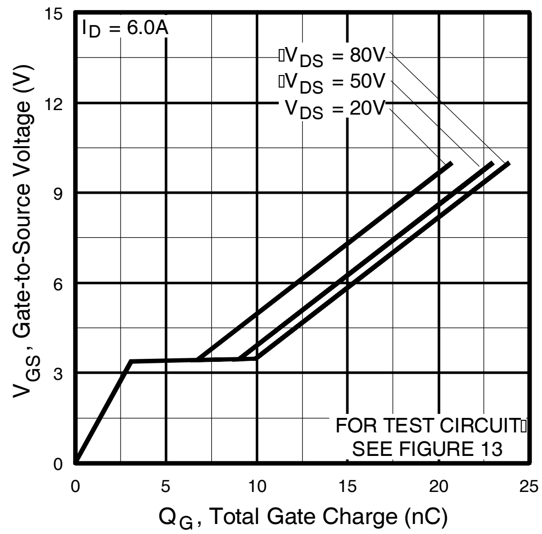


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

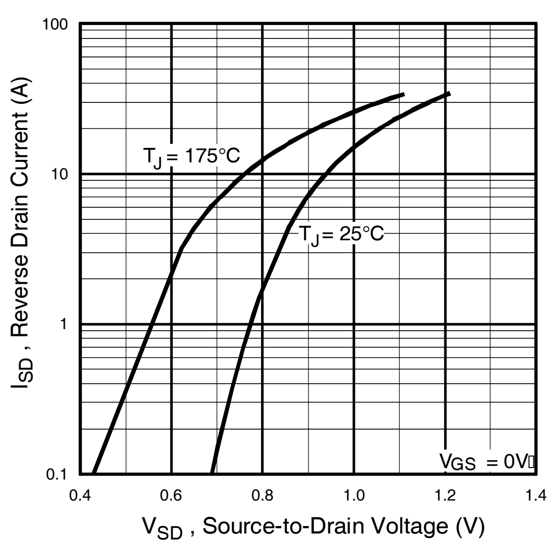


Fig 7. Typical Source-Drain Diode Forward Voltage

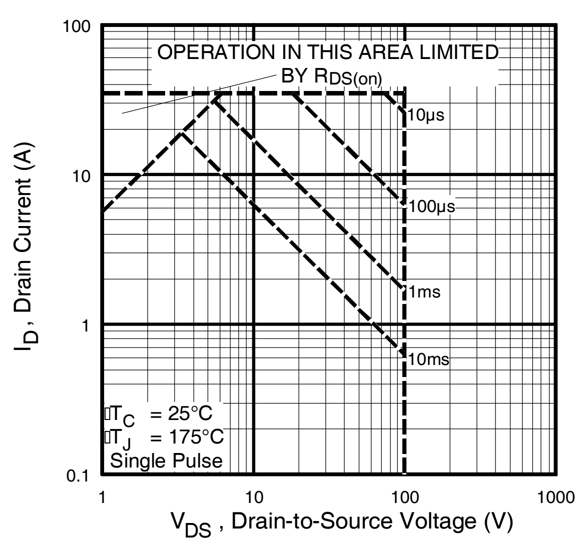


Fig 8. Maximum Safe Operating Area

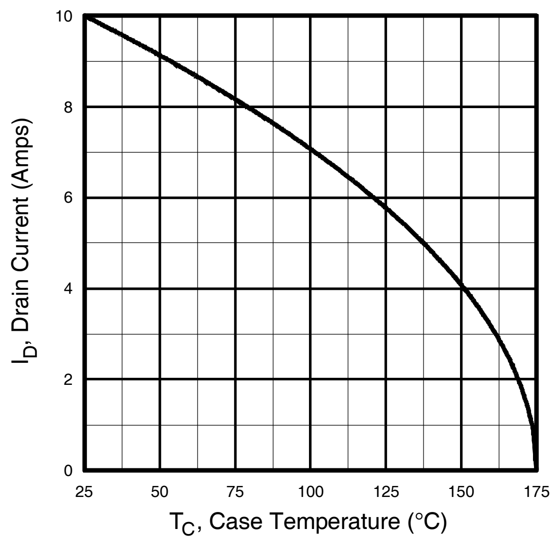


Fig 9. Maximum Drain Current Vs. Case Temperature

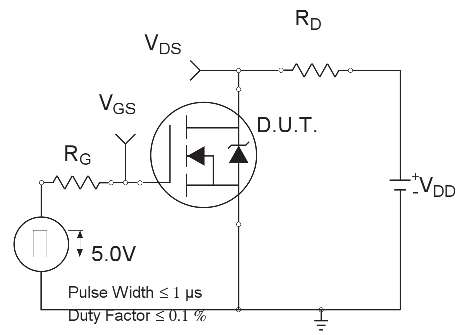


Fig 10a. Switching Time Test Circuit

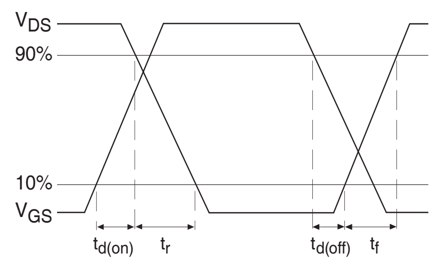


Fig 10b. Switching Time Waveforms

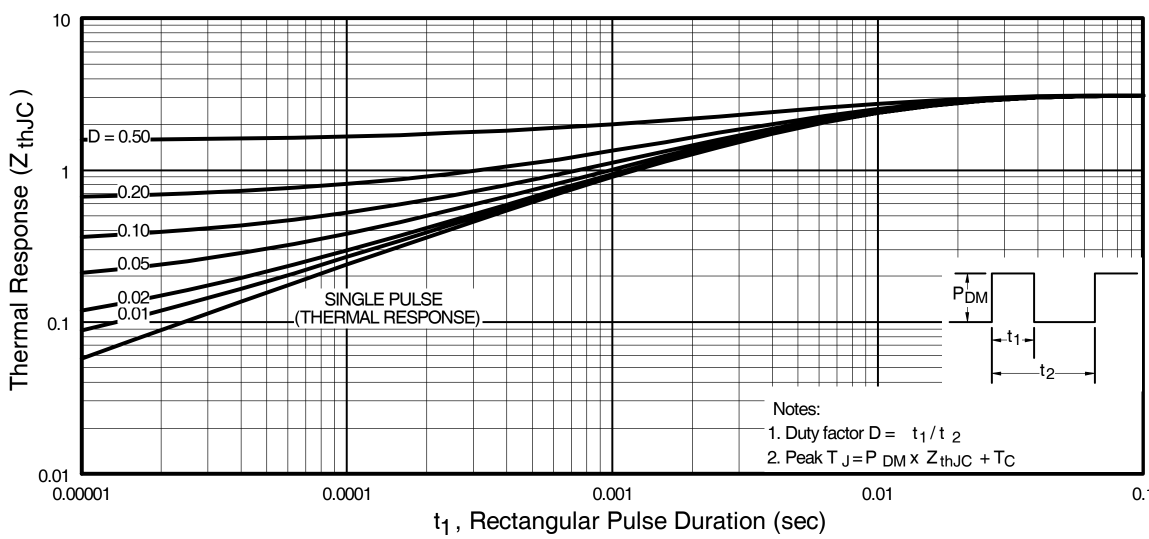


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

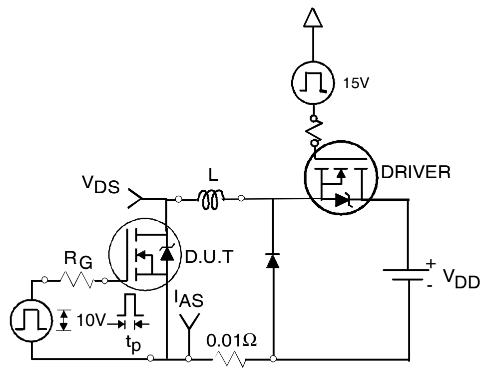


Fig 12a. Unclamped Inductive Test Circuit

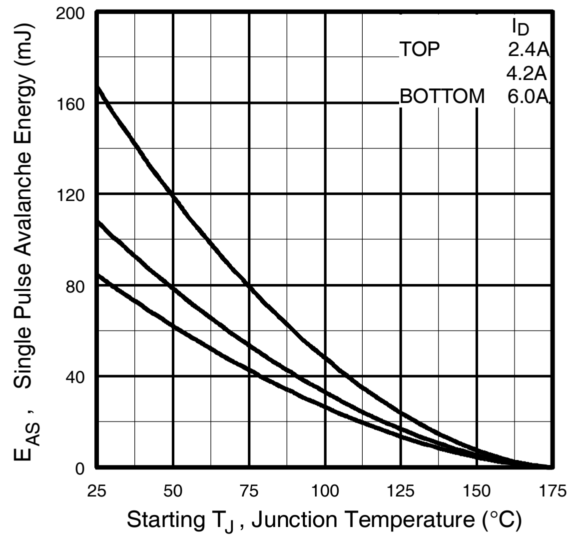


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

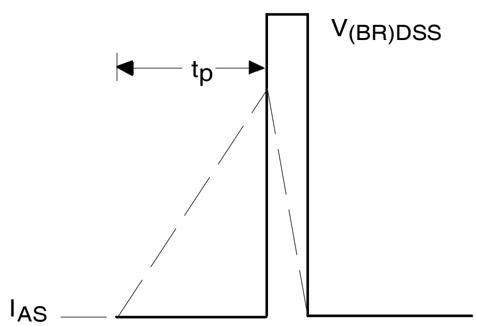


Fig 12b. Unclamped Inductive Waveforms

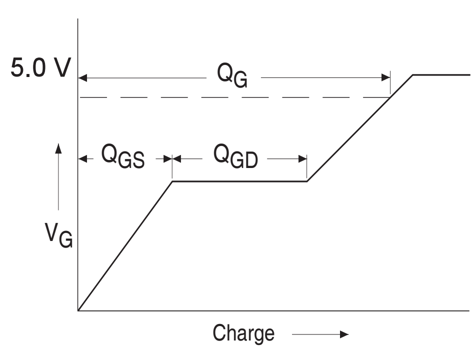


Fig 13a. Basic Gate Charge Waveform

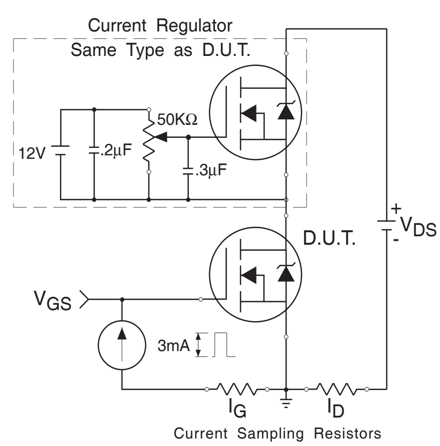
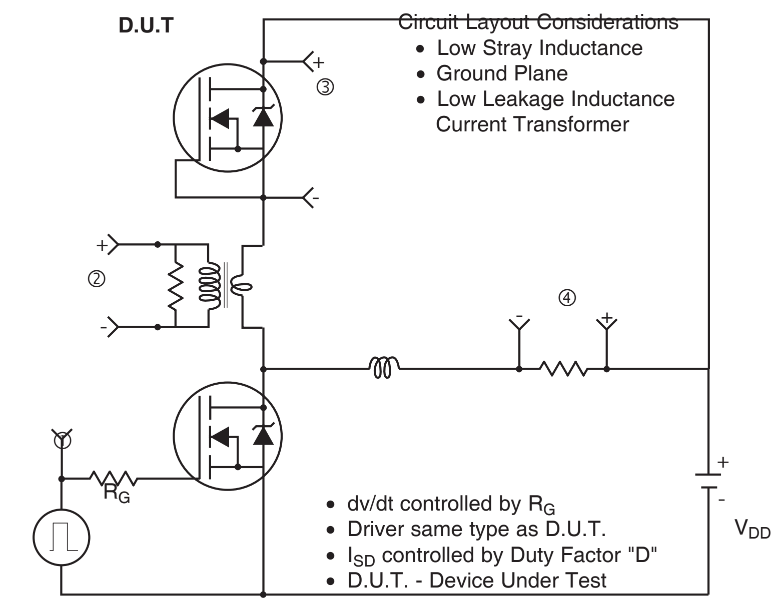
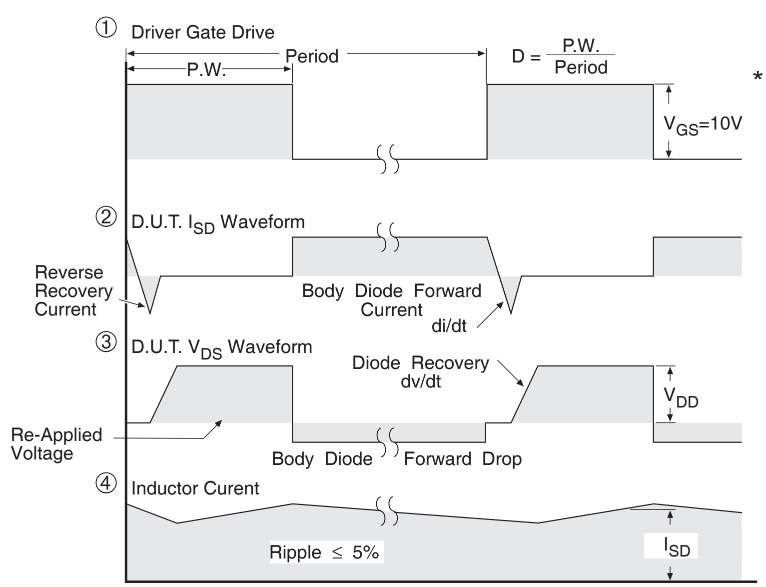


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



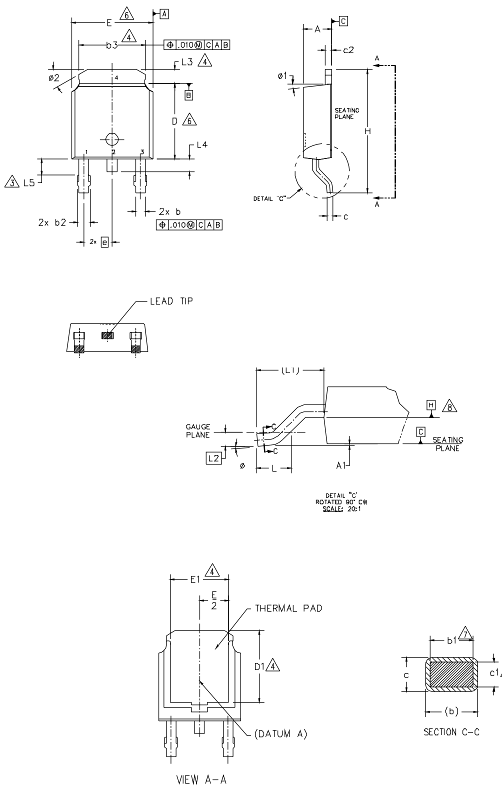


* V_{GS} = 5V for Logic Level Devices

Fig 14. For N-Channel HEXFETS

D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2.- DIMENSION ARE SHOWN IN INCHES [MILLIMETERS].
3.- LEAD DIMENSION UNCONTROLLED IN L5.
4.- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
6.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
7.- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
8.- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	–	0.13	–	.005	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	7
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	7
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	6
D1	5.21	–	.205	–	4
E	6.35	6.73	.250	.265	6
E1	4.32	–	.170	–	4
e	2.29 BSC		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 BSC		.108 REF.		
L2	0.51 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	4
L4	–	1.02	–	.040	
L5	1.14	1.52	.045	.060	3
ø	0°	10°	0°	10°	
ø1	0°	15°	0°	15°	
ø2	25°	35°	25°	35°	

LEAD ASSIGNMENTS

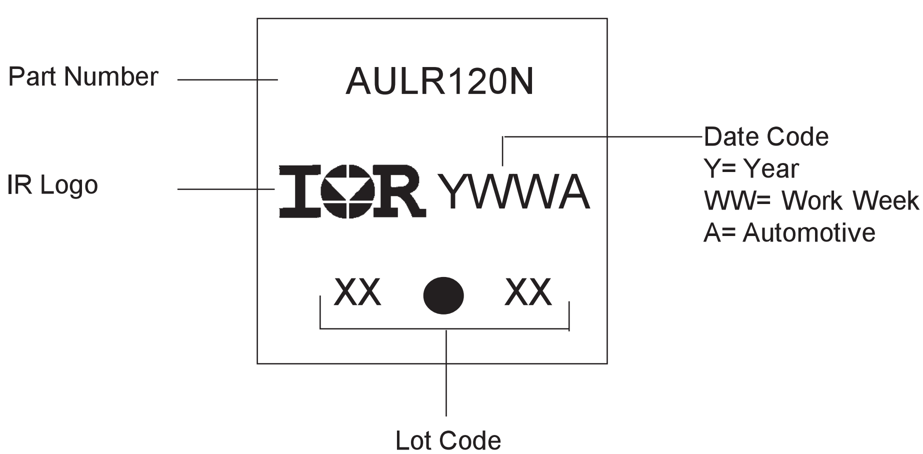
HEXFET

1.- GATE
2.- DRAIN
3.- SOURCE
4.- DRAIN

IGBT & CoPAK

1.- GATE
2.- COLLECTOR
3.- EMITTER
4.- COLLECTOR

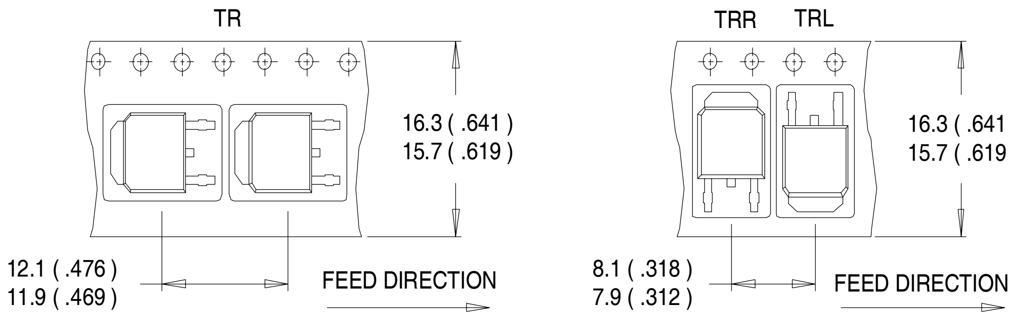
D-Pak Part Marking Information



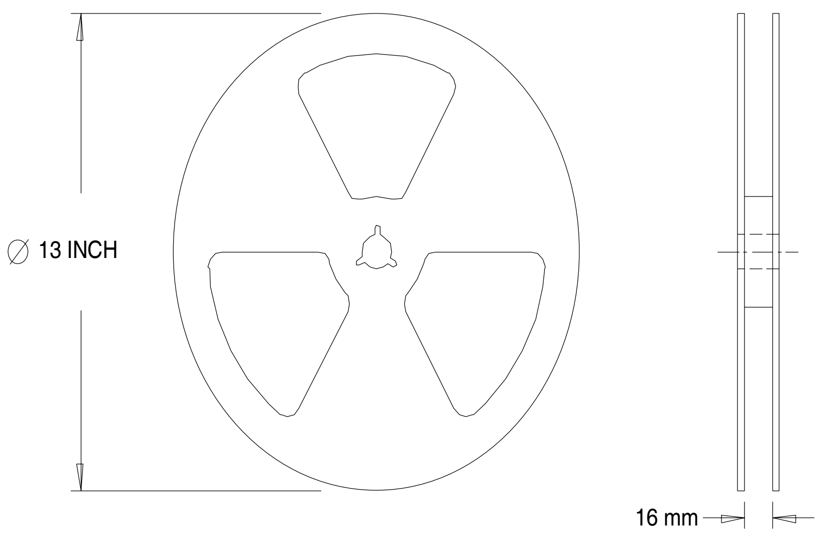
Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :
1. OUTLINE CONFORMS TO EIA-481.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Ordering Information

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRLR120N	Dpak	Tube	75	AUIRLR120N
		Tape and Reel	2000	AUIRLR120NTR
		Tape and Reel Left	3000	AUIRLR120NTRL
		Tape and Reel Right	3000	AUIRLR120NTRR

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http://www.irf.com/technical-info/

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